

## 500V 1A N-Channel Enhancement Mode Power MOSFET

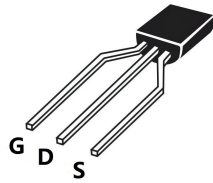
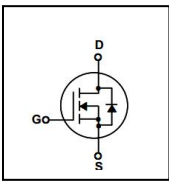
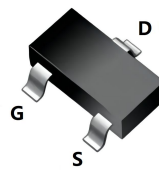
### General Description

BXP1N50 is Bridgelux high voltage MOSFET family based on advanced planar DMOS technology. This advanced MOSFET family has optimized on-state resistance, and also provides superior switching performance and higher avalanche energy strength. This device family is suitable for high efficiency switch mode power supplies.

### FEATURES

- $R_{DS(ON)} \leq 12 \Omega$  @  $V_{GS}=10V, I_D=0.5A$
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Fast switching capability
- Lead free product is acquired

### SYMBOL


**TO-92**

**SOT-23L**

### ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXP1N50G	TO-92	Ammopack
BXP1N50L	SOT-23L	Reel

### ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating	Unit	
		BXP1N50G/BXP1N50L		
Drain-Source Voltage	$V_{DSS}$	500	V	
Drain Current	$I_D$	Continuous ( $T_C = 25^\circ\text{C}$ )	1	A
		Continuous ( $T_C = 100^\circ\text{C}$ )	0.6	A
Drain Current	$I_{DM}$	4	A	
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V	
Avalanche Energy	Single Pulse (Note2)	$E_{AS}$	11	mJ
Avalanche Current (Note1)	$I_{AR}$	1	A	
Peak Diode Recovery $dv/dt$ (Note3)	$dv/dt$	5	V/ns	
Power Dissipation (Note 2)	$P_D$	$T_C = 25^\circ\text{C}$	3	W
		Derate above $25^\circ\text{C}$	0.024	W/ $^\circ\text{C}$
Maximum Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ\text{C}$	

- Note:**
1. Repetitive Rating: Pulse width limited by maximum junction temperature
  2.  $L=10\text{mH}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25 \Omega$ , Starting  $T_J = 25^\circ\text{C}$
  3.  $I_{SD} \leq 1\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Parameter	Symbol	Max.	Unit
		BXP1N50G/BXP1N50L	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	42	$^{\circ}\text{C} / \text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^{\circ}\text{C} / \text{W}$

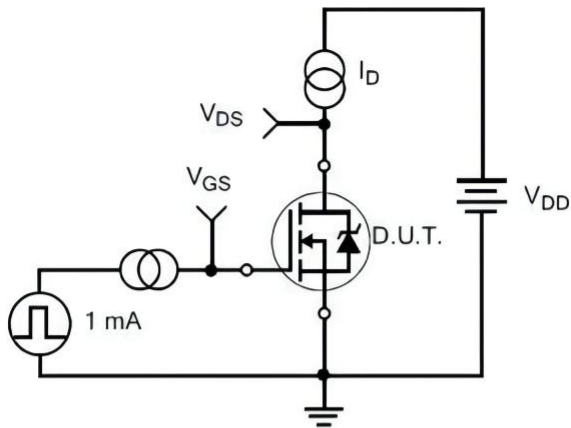
**ELECTRICAL CHARACTERISTICS** ( $T_J=25^{\circ}\text{C}$ , unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	500			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=500V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=400V, T_C = 125^{\circ}\text{C}$			100	$\mu A$
Gate-Body Leakage Current, Forward	$I_{GSS}$	$V_{GS}=30V$			100	nA
Gate-Body Leakage Current, Reverse		$V_{GS}=-30V$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250 \mu A$		0.6		$V/^{\circ}\text{C}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.5A$		9.5	12	$\Omega$
Forward Transconductance (Note4)	$g_{FS}$	$V_{DS} = 30V, I_D=0.5A$		0.7		S
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{MHz}$		80		pF
Output Capacitance	$C_{OSS}$			10		pF
Reverse Transfer Capacitance	$C_{RSS}$			2		pF
<b>SWITCHING PARAMETERS</b>						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250V, I_D=1A, V_{GS} =$ $10V, R_G=25\Omega$ (Note4,5)		8		ns
Turn-ON Rise Time	$t_R$			9		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			22		ns
Turn-OFF Fall-Time	$t_F$			16		ns
Total Gate Charge(Note5)	$Q_G$	$V_{DS} = 250V, V_{GS} = 10V, I_D$ $=1A$ (Note4,5)		5		nC
Gate Source Charge	$Q_{GS}$			0.8		nC
Gate Drain Charge	$Q_{GD}$			1.9		nC
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=1A, V_{GS}=0V$			1.4	V
Diode Continuous Forward Current	$I_S$				1	A
Pulsed Drain-Source Current	$I_{SM}$				4	A
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0V, I_{SD} = 1A$		40		ns
Reverse Recovery Charge	$Q_{RR}$	$di/dt=100 A/\mu s$ (Note4,5)		0.06		$\mu C$

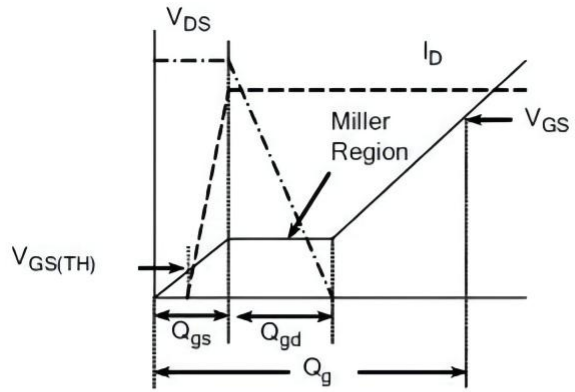
Note: 4. Pulse Test : Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$

5. Essentially independent of operating temperature

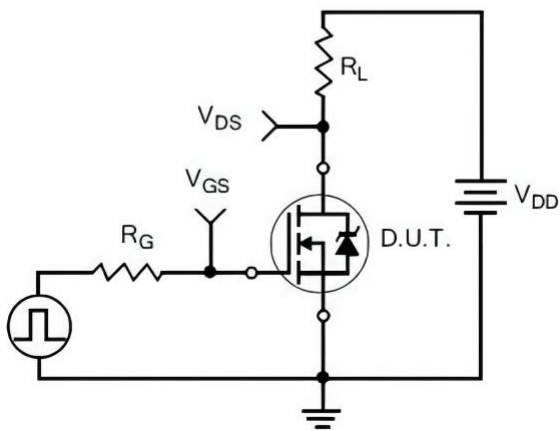
TEST CIRCUITS AND WAVEFORMS



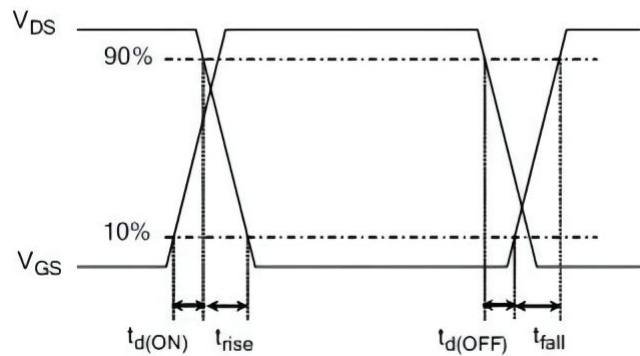
Gate Charge Test Circuit



Gate Charge Waveform

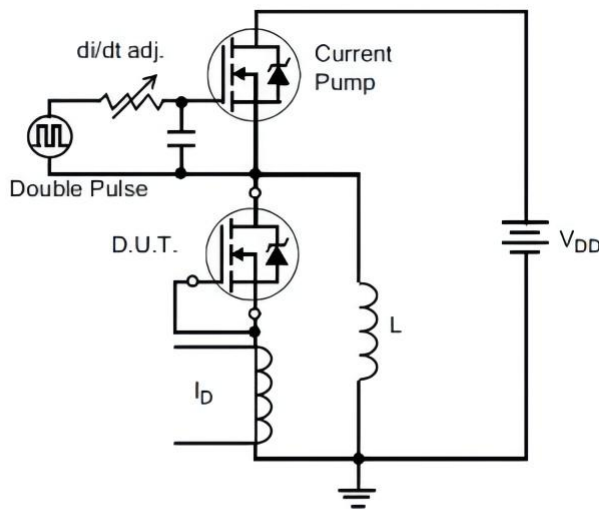


Resistive Switching Test Circuit

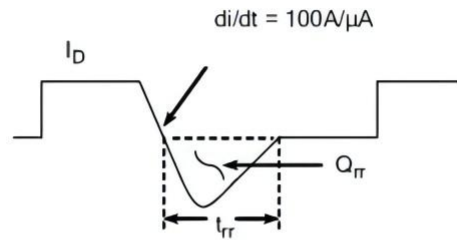


Resistive Switching Waveforms

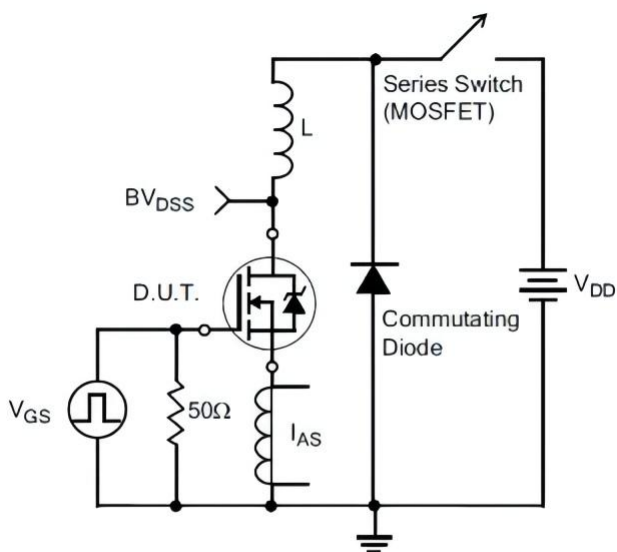
TEST CIRCUITS AND WAVEFORMS(Cont.)



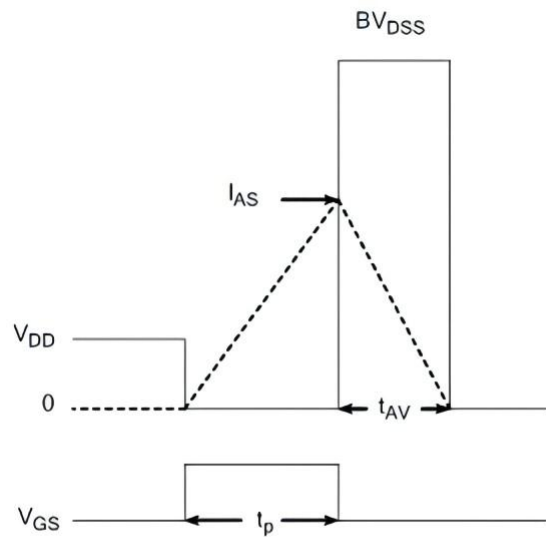
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform



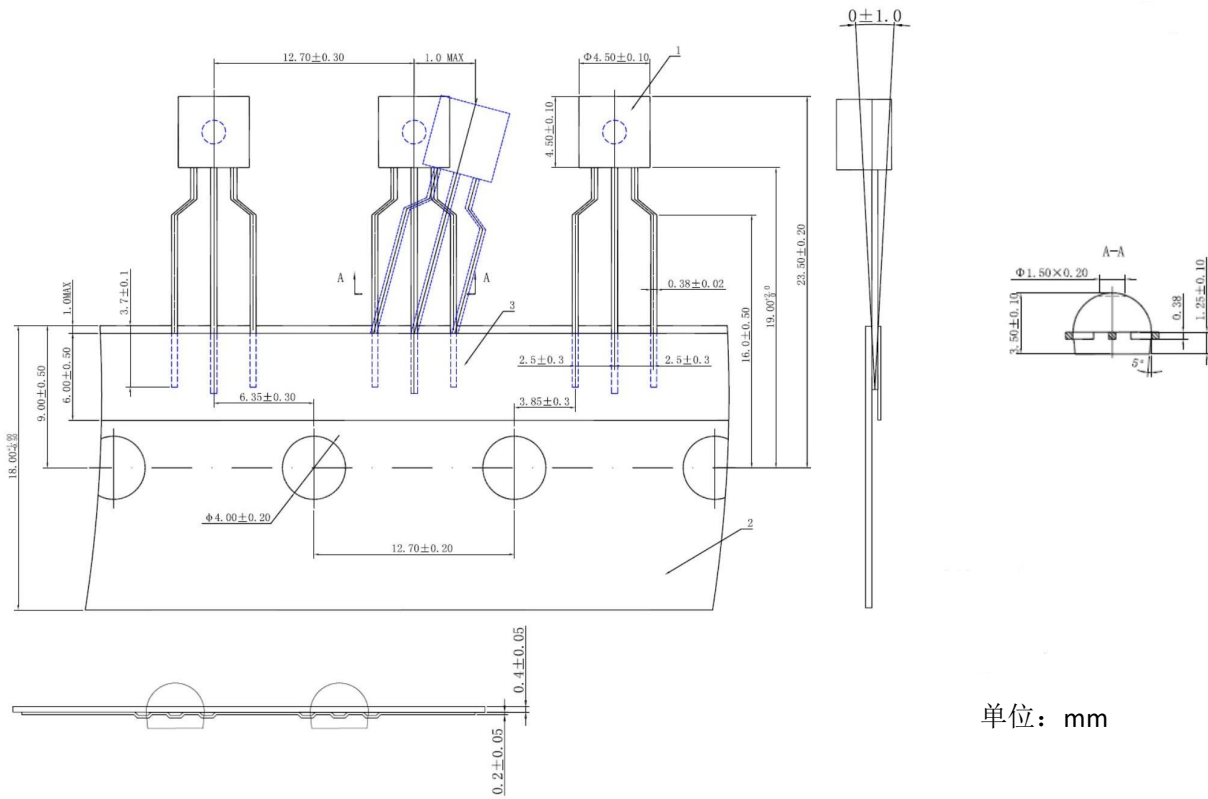
Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

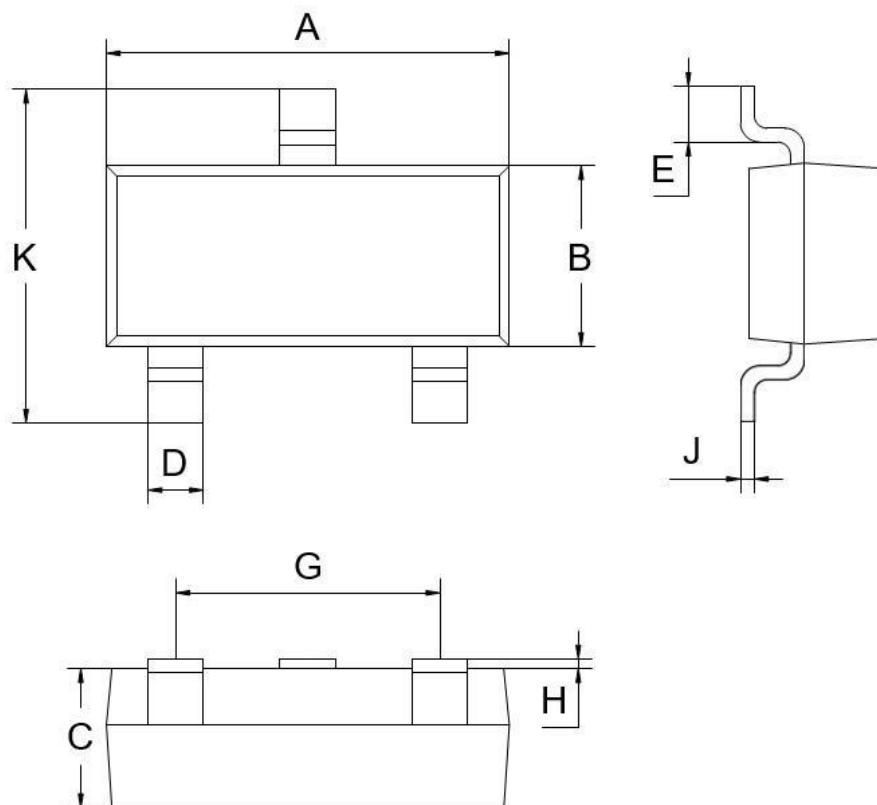
Unclamped Inductive Switching Waveforms

### TO-92 Package



单位: mm

### SOT-23L Package



SOT-23L		
Dim	Min	Max
A	2.80	3.02
B	1.50	1.70
C	1.05	1.15
D	0.28	0.5
E	0.28	0.6
G	1.80	2.00
H	0.02	0.10
J	0.1	0.2
K	2.70	3.00
All Dimensions in mm		

## Revision history

### Document revision history

Date	Revision	Changes
20-Jan-2022	1.0	First release
27-Jan-2022	1.1	Update parameter

**Disclaimers:**

Bridgelux WuXi has made reasonable commercial efforts to ensure that the information given in this data sheet is correct. However, it must clearly be understood that such information is for guidance only and does not constitute any representation or form part of any offer or contract.

For documents and material available from this data sheet, Bridgelux WuXi does not warrant or assume any legal liability or responsibility for the accuracy, completeness, or usefulness of any information, product, technology or process disclosed hereunder.

Bridgelux WuXi reserves the rights to at its own discretion to make any changes or improvements to this data sheet. Unless said data sheet is incorporated into the formal contract, any customer should not rely on the information as any specification or product parameters duly committed by Bridgelux WuXi. Customers are hereby advised to verify that the information contained herein is current and complete before the entering of any contract or acknowledgement of any purchase order. Accordingly, all products specified hereunder shall be sold subject to Bridgelux WuXi's terms and conditions supplied at the time of order acknowledgement. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessarily performed.

Bridgelux WuXi does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information contained herein shall be only permissible if such reproduction is without any modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. Bridgelux WuXi is not responsible or liable for such altered documentation.

Resale of Bridgelux WuXi's products with statements different from or beyond the parameters stated by Bridgelux WuXi for that product or service voids all express or implied warranties for the associated Bridgelux WuXi's product or service and is unfair and deceptive business practice. Bridgelux WuXi is not responsible or liable for any such statements.

Bridgelux WuXi's products are not authorized for use as critical components in life support devices or systems without the express written approval of Bridgelux WuXi. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.